

Electronic Supplementary Information

Enhancement of crystalline quality and solar-blind photodetection characteristic of ϵ -Ga₂O₃ Film by introducing Zn impurity

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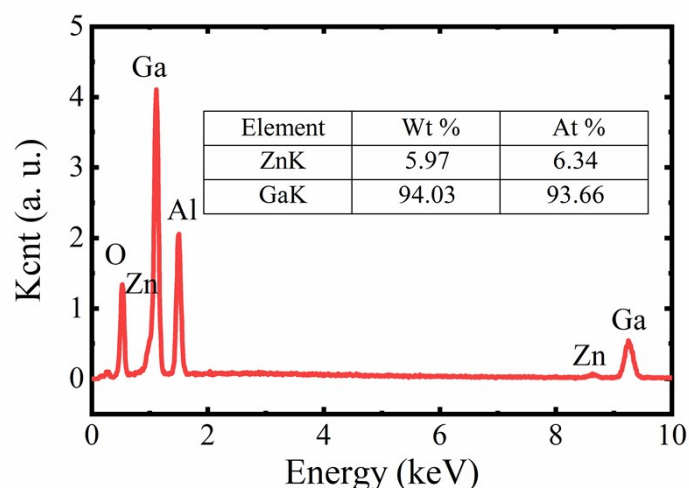


Figure S1 EDS spectrum of ϵ -Ga₂O₃:Zn.

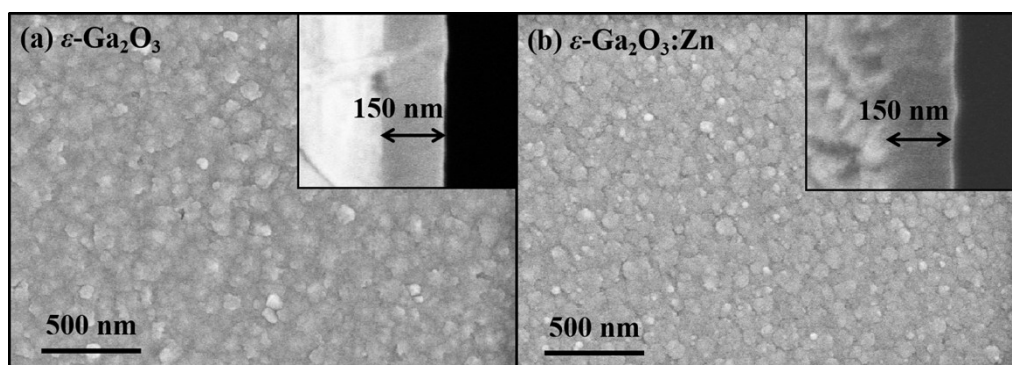


Figure S2 SEM images of (a) pure ϵ -Ga₂O₃ and (b) ϵ -Ga₂O₃:Zn.

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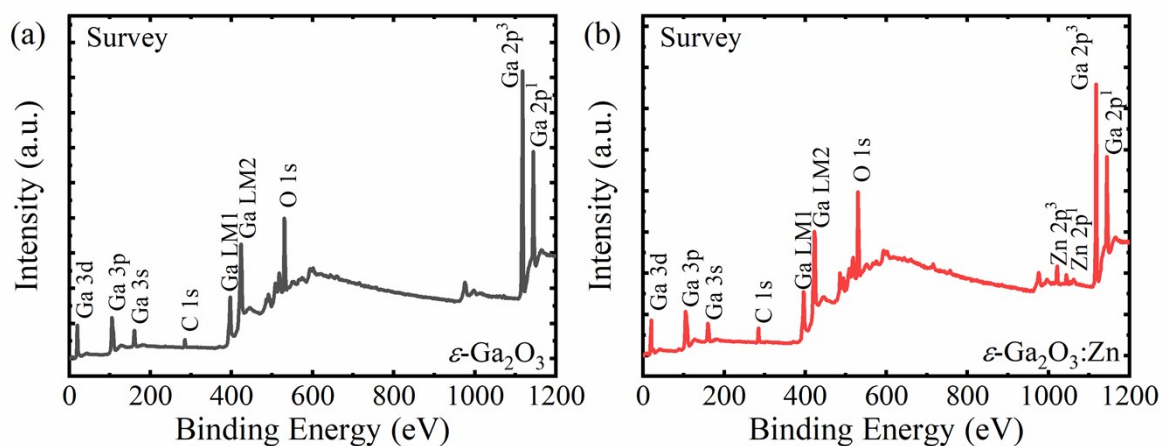


Figure S3 XPS survey spectra of (a) pure ϵ -Ga₂O₃ and (b) ϵ -Ga₂O₃:Zn.

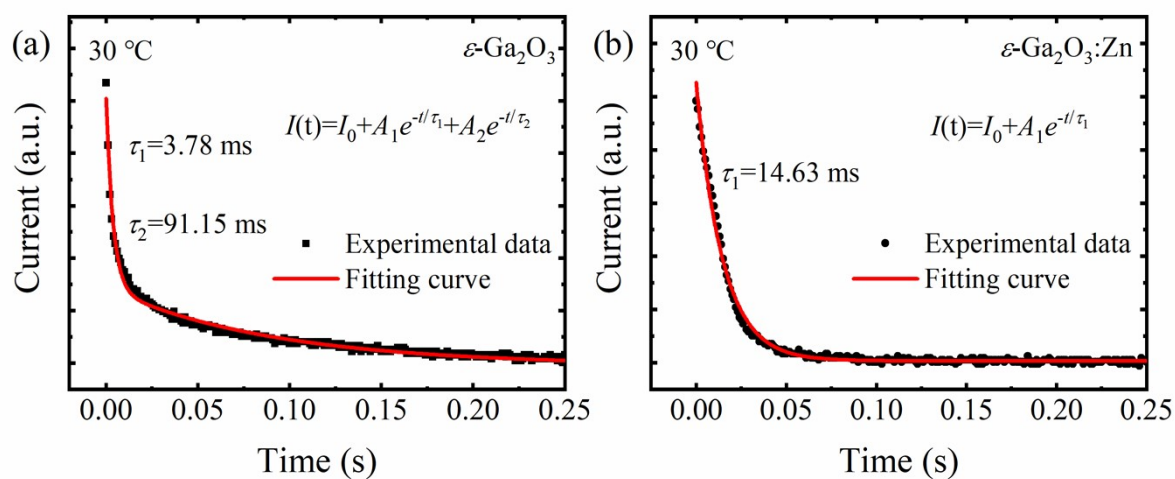


Figure S4 Typical decay curves of (a) ϵ -Ga₂O₃ and (b) Zn-doped ϵ -Ga₂O₃ detectors at 30 °C.